

Major Ratings and Characteristics

$I_{F(AV)}$	2.0A
V_{RRM}	50 V to 1000 V
I_{FSM}	50 A
t_{rr}	50nS,75nS
V_F	1.0V,1.3V,1.7V
$T_j \text{ max.}$	150 °C



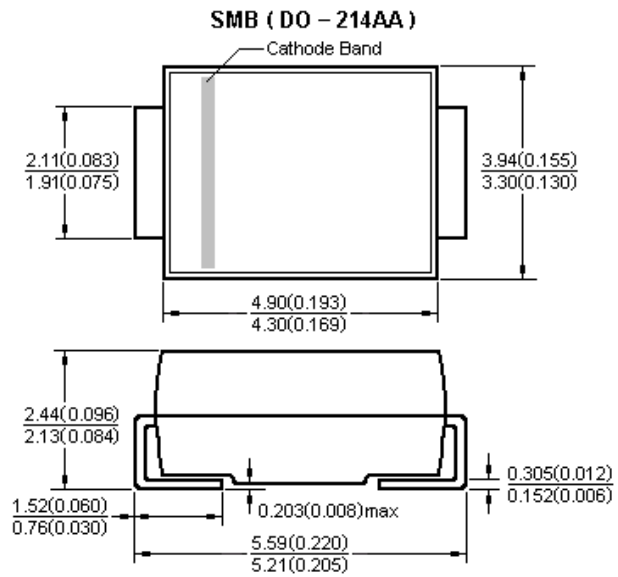
SMB (DO - 214AA)

Features

- Low profile package
- Ideal for automated placement
- Glass passivated chip junctions
- Ultrafast reverse recovery time
- Low switching losses, high efficiency
- High forward surge capability
- High temperature soldering:
260°C/10 seconds at terminals
- Component in accordance to
RoHS 2002/95/1 and WEEE 2002/96/EC

Mechanical Date

- **Case:** JEDEC DO-214AA molded plastic body over passivated chip
- **Terminals:** Solder plated, solderable per J-STD-002B and JESD22-B102D
- **Polarity:** Laser band denotes cathode end



Dimensions in millimeters and (inches)

Maximum Ratings & Thermal Characteristics & Electrical Characteristics

($T_A = 25\text{ °C}$ unless otherwise noted)

	Symbol	US2A	US2B	US2D	US2G	US2J	US2K	US2M	UNIT
Maximum repetitive peak reverse voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS voltage	V_{RMS}	35	70	140	280	420	560	700	V
Maximum DC blocking voltage	V_{DC}	50	100	200	400	600	800	1000	V
Maximum average forward rectified current	$I_{F(AV)}$	2							A
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load	I_{FSM}	50							A
Maximum instantaneous forward voltage at 2.0A	V_F	1.0		1.3		1.7			V
Maximum DC reverse current $T_A = 25\text{ °C}$ at Rated DC blocking voltage $T_A = 100\text{ °C}$	I_R	10.0 50							μA
Maximum reverse recovery time at $I_F = 0.5\text{ A}$, $I_R = 1.0\text{ A}$, $I_{rr} = 0.25\text{ A}$	t_{rr}	50				75			nS
Typical junction capacitance at 4.0 V, 1MHz	C_J	15							pF
Thermal resistance from junction to lead	$R_{\theta JL}$	95							$^{\circ}\text{C} / \text{W}$
Operating junction and storage temperature range	T_J, T_{STG}	-55 to +150							$^{\circ}\text{C}$

Characteristic Curves ($T_A=25\text{ }^\circ\text{C}$ unless otherwise noted)

